

Title (en)

METHOD FOR CREATING A CARBON LAYER ON A STARTING STRUCTURE AND MICRO-ELECTROMECHANICAL OR SEMICONDUCTOR STRUCTURE

Title (de)

VERFAHREN ZUM ERZEUGEN EINER KOHLENSTOFFSCHICHT AUF EINER AUSGANGSSTRUKTUR UND MIKROELEKTROMECHANISCHE ODER HALBLEITER-STRUKTUR

Title (fr)

PROCÉDÉ POUR CRÉER UNE COUCHE DE CARBONE SUR UNE STRUCTURE DE DÉPART ET STRUCTURE MICROÉLECTROMÉCANIQUE OU SEMI-CONDUCTRICE

Publication

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Application

**EP 15797674 A 20151120**

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Abstract (en)

[origin: WO2016116195A1] The invention relates to a method for creating a micro-electromechanical or semiconductor structure, comprising the following steps: providing an starting structure, the surface of which has at least sections consisting of silicon dioxide; providing a starting material, or a mixture of several starting materials, which release a mixture of carbon, silicon and chlorine in an LPCVD process; introducing the starting structure and the one, or the mixture of, starting material into the LPCVD process; and thereby separating a carbon layer on the sections of the starting structure consisting of silicon dioxide. The invention also relates to a micro-electromechanical or semiconductor structure which is produced according to the method.

IPC 8 full level

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